

Satinder K Sharma

List of Publications by Year in descending order

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papers

362
citations

840776

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32
times ranked

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citing authors

#	ARTICLE	IF	CITATIONS
1	Charge Trapping Analysis of Metal/Al ₂ O ₃ /SiO ₂ /Si, Gate Stack for Emerging Embedded Memories. IEEE Transactions on Device and Materials Reliability, 2017, 17, 80-89.	2.0	39
2	Integration of Ferroelectric Materials: An Ultimate Solution for Next-Generation Computing and Storage Devices. ACS Applied Electronic Materials, 2021, 3, 2862-2897.	4.3	35
3	Low voltage & controlled switching of MoS ₂ -GO resistive layers based ReRAM for non-volatile memory applications. Semiconductor Science and Technology, 2019, 34, 085009.	2.0	30
4	Development of Nickel-Based Negative Tone Metal Oxide Cluster Resists for Sub-10 nm Electron Beam and Helium Ion Beam Lithography. ACS Applied Materials & Interfaces, 2020, 12, 19616-19624.	8.0	30
5	Organotin in Nonchemically Amplified Polymeric Hybrid Resist Imparts Better Resolution with Sensitivity for Next-Generation Lithography. ACS Applied Polymer Materials, 2020, 2, 1790-1799.	4.4	21
6	Facile Synthesis of 2D-HfS ₂ Flakes for μ -IDE-Based Methanol Sensor: Fast Detection at Room Temperature. IEEE Sensors Journal, 2019, 19, 9090-9096.	4.7	18
7	Resists for Helium Ion Beam Lithography: Recent Advances. ACS Applied Electronic Materials, 2020, 2, 3805-3817.	4.3	16
8	Organiodine Functionality Bearing Resists for Electron-Beam and Helium Ion Beam Lithography: Complex and Sub-16 nm Patterning. ACS Applied Electronic Materials, 2021, 3, 1996-2004.	4.3	16
9	Organic-inorganic hybrid photoresists containing hexafluoroantimonate: design, synthesis and high resolution EUV lithography studies. Materials Chemistry Frontiers, 2017, 1, 2613-2619.	5.9	13
10	A photoacid generator integrated terpolymer for electron beam lithography applications: sensitive resist with pattern transfer potential. Materials Chemistry Frontiers, 2017, 1, 1895-1899.	5.9	11
11	Nitrogen doped multilayer photo catalytically reduced graphene oxide floating gate: Al/PMMA/NrGO/SiO ₂ /p-Si/Au based hybrid gate stack for non volatile memory applications. Organic Electronics, 2017, 51, 48-53.	2.6	11
12	Realization and Performance Analysis of Facile-Processed μ -IDE-Based Multilayer HfS ₂ /HfO ₂ Transistors. IEEE Transactions on Electron Devices, 2019, 66, 3236-3241.	3.0	11
13	Substrate orientation dependent current transport mechanisms in α -Ga ₂ O ₃ /Si based Schottky barrier diodes. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, .	2.1	11
14	Probing Ferrimagnetic Semiconductor with Enhanced Negative Magnetoresistance: 2D Chromium Sulfide. Advanced Electronic Materials, 2021, 7, 2001116.	5.1	11
15	Highly sensitive electrochemical sensing of neurotransmitter dopamine from scalable UV irradiation-based nitrogen-doped reduced graphene oxide-modified electrode. Bulletin of Materials Science, 2020, 43, 1.	1.7	10
16	High-performance CSA-PANI based organic phototransistor by elastomer gratings. Organic Electronics, 2018, 57, 14-20.	2.6	9
17	Integration of graphene oxide buffer layer/graphene floating gate for wide memory window in Pt/Ti/Al ₂ O ₃ /GO/graphene/SiO ₂ /p-Si/Au non-volatile (FLASH) applications. Applied Physics Letters, 2018, 112, .	3.3	9
18	Low-Current-Density Magnetic Tunnel Junctions for STT-RAM Application Using MgO ₂ Tunnel Barrier. IEEE Transactions on Electron Devices, 2020, 67, 125-132.	3.0	9

#	ARTICLE	IF	CITATIONS
19	A Steep Slope MBE-Grown Thin p-Ge Channel FETs on Bulk Ge-on-Si Using HZO Internal Voltage Amplification. IEEE Transactions on Electron Devices, 2022, 69, 2725-2731.	3.0	8
20	Functionalized Ag Nanoparticles Embedded in Polymer Resists for High-Resolution Lithography. ACS Applied Nano Materials, 2020, 3, 8651-8661.	5.0	7
21	Realization of Large Area Co ₂₀ Fe ₆₀ B ₂₀ -Based Perpendicular Magnetic Tunnel Junction for CMOS Compatible Device Application. ACS Applied Electronic Materials, 2019, 1, 2268-2278.	4.3	6
22	Maskless lithography: an approach to SU-8 based sensitive and high-g Z-axis polymer MEMS accelerometer. Microsystem Technologies, 2021, 27, 2925-2934.	2.0	6
23	Enhanced mechanical properties of the high-resolution EUVL patterns of hybrid photoresists containing hexafluoroantimonate. Microelectronic Engineering, 2018, 194, 100-108.	2.4	4
24	Highly UV sensitive Sn nanoparticles blended with polyaniline onto micro-interdigitated electrode array for UV-C detection applications. Journal of Materials Science: Materials in Electronics, 2019, 30, 7534-7542.	2.2	4
25	Low-Latency and Reconfigurable VLSI-Architectures for Computing Eigenvalues and Eigenvectors Using CORDIC-Based Parallel Jacobi Method. IEEE Transactions on Very Large Scale Integration (VLSI) Systems, 2022, 30, 1020-1033.	3.1	4
26	Alternate lanthanum oxide/silicon oxynitride-based gate stack performance enhancement due to ultrathin oxynitride interfacial layer for CMOS applications. Journal of Materials Science: Materials in Electronics, 2020, 31, 1986-1995.	2.2	3
27	NrGO Floating Gate/SiOXNY Tunneling Layer Stack for Nonvolatile Flash Memory Applications. IEEE Transactions on Device and Materials Reliability, 2020, 20, 570-575.	2.0	3
28	Metal (Pt)/ferroelectric (SrBi ₂ Ta ₂ O ₉)/insulator (La ₂ O ₃)/semiconductor (Si), MFIS structures for nonvolatile memory applications. Applied Physics Letters, 2021, 119, .	3.3	3
29	Nanoscale Probing of Surface Charges in Functional Copper-Metal Organic Clusters by Kelvin Probe Force Microscopy for Field-Effect Transistors. Advanced Materials Interfaces, 2021, 8, 2100529.	3.7	2
30	A Discrete-Time MOS Parametric Amplifier-Based Chopped Signal Demodulator. IEEE Transactions on Very Large Scale Integration (VLSI) Systems, 2020, 28, 2268-2279.	3.1	1
31	Integration of High-Performance Cost-Effective Copper-Metal-Organic-Nanocluster-based Gate Dielectric for Next-Generation CMOS Applications. Advanced Electronic Materials, 2021, 7, 2000835.	5.1	1
32	Digitally Assisted Secondary Switch-and-Compare Technique for a SAR ADC. IEEE Transactions on Circuits and Systems II: Express Briefs, 2021, 68, 2317-2321.	3.0	0